Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... PNPN devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

- · Passivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Recommended Electrical Replacement for C106





ΑK

(TO-225AA)

STYLE 2

2N6237 thru

2N6241

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted.)

Rating		Symbol	Value	Unit	
*Repetitive Peak Forward and Reverse Blockin (1/2 Sine Wave) (R _{GK} = 1000 ohms, T _C = -40 to +110°C)	g Voltage ⁽¹⁾ 2N6237 2N6238 2N6239 2N6240 2N6241	VDRM or VRRM	50 100 200 400 600	Volts	
*Non-repetitive Peak Reverse Blocking Voltage (1/2 Sine Wave, R _{GK} = 1000 ohms, T _C = -40 to +110°C)	2N6237 2N6238 2N6239 2N6240 2N6241	VRSM	100 150 250 450 650	Volts	
*Average On-State Current $(T_C = -40 \text{ to } +90^{\circ}\text{C})$ $(T_C = +100^{\circ}\text{C})$		IT(AV)	2.6 1.6	Amps	
*Surge On-State Current (1/2 Sine Wave, 60 Hz, $T_C = +90^{\circ}C$) (1/2 Sine Wave, 1.5 ms, $T_C = +90^{\circ}C$)		ITSM	25 35	Amps	
Circuit Fusing (t = 8.3 ms)		l ² t	2.6	A ² s	
*Peak Gate Power (Pulse Width = 10 μs, T _C = 90°C)		PGM	0.5	Watts	

*Indicates JEDEC Registered Data.

(continued)

VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



2N6237 thru 2N6241

MAXIMUM RATINGS — continued ($T_C = 25^{\circ}C$ unless otherwise noted.)

Symbol	Value	Unit
PG(AV)	0.1	Watt
I _{GM}	0.2	Amp
V _{RGM}	6	Volts
Tj	-40 to +110	°C
T _{stg}	-40 to +150	°C
—	6	in. lb.
	PG(AV) IGM VRGM TJ	PG(AV) 0.1 IGM 0.2 VRGM 6 TJ -40 to +110 Tstg -40 to +150

Characteristic		Min	Max Unit	
*Thermal Resistance, Junction to Case	R _{θJC}		3	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		75	°C/W

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ and $R_{GK} = 1000$ ohms unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
*Peak Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM}) $T_C = 25^{\circ}C$ $T_C = 110^{\circ}C$	I _{DRM} , I _{RRM}			10 200	μΑ μΑ
*Peak Forward "On" Voltage (I _{TM} = 8.2 A Peak, Pulse Width = 1 to 2 ms, 2% Duty Cycle)	V _{TM}	-	—	2.2	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ (V _{AK} = 12 Vdc, R _L = 24 Ohms) * (V _{AK} = 12 Vdc, R _L = 24 Ohms, T _C = -40° C)	IGT			200 500	μΑ
Gate Trigger Voltage (Continuous dc) (Source Voltage = 12 V, R _S = 50 Ohms) *(V _{AK} = 12 Vdc, R _L = 24 Ohms, T _C = -40°C)	V _{GT}	-	—	1	Volts
Gate Non-Trigger Voltage (V _{AK} = Rated V _{DRM} , R _L = 100 Ohms, T _C = 110°C)	V _{GD}	0.2			Volts
Holding Current $(V_{AK} = 12 \text{ Vdc}, \text{ I}_{GT} = 2 \text{ mA})$ $T_C = 25^{\circ}C$ * (Initiating On-State Current = 200 mA) $T_C = -40^{\circ}C$	ι _Η			5 10	mA
*Total Turn-On Time (Source Voltage = 12 V, $R_S = 6 \text{ k Ohms}$) ($I_{TM} = 8.2 \text{ A}$, $I_{GT} = 2 \text{ mA}$, Rated V_{DRM}) (Rise Time = 20 ns, Pulse Width = 10 µs)	^t gt	-	2	—	μs
Forward Voltage Application Rate (V _D = Rated V _{DRM} , T _C = 110°C)	dv/dt	_	10		V/µs

*Indicates JEDEC Registered Data.

 Torque rating applies with use of compression washer (B52200F006 or equivalent). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common. (See AN-209 B)
For soldering purposes (either terminal connection or device mounting), soldering temperatures shall not exceed +200°C. For optimum results an activated flux (oxide removing) is recommended.

2. Measurement does not include RGK current.



PACKAGE DIMENSIONS



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